

BRYM3N50AF

/ Absolute Maximum Ratings($T_a=25^\circ\text{C}$)

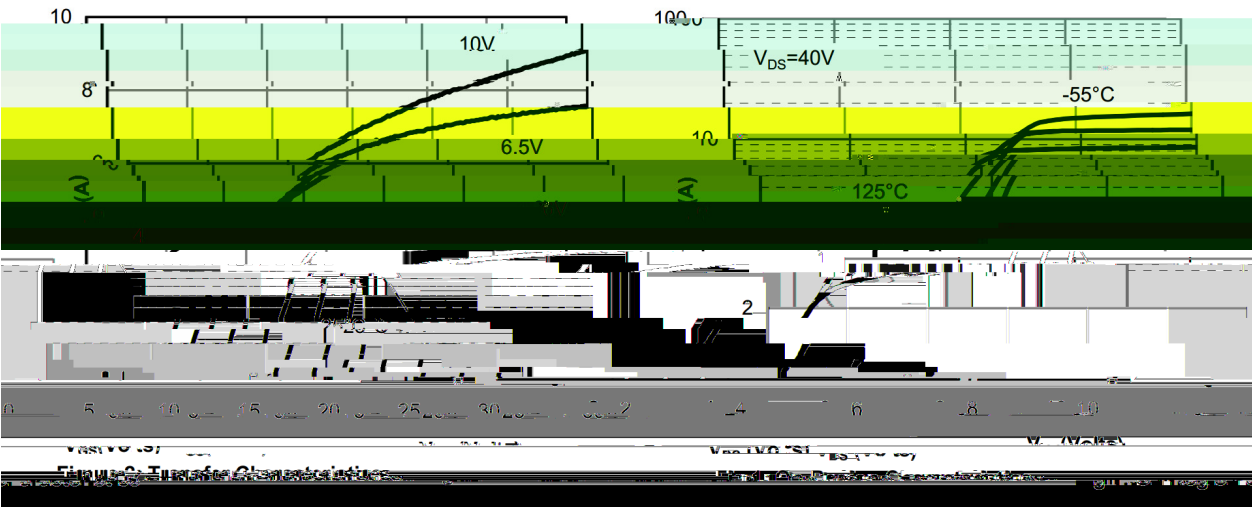
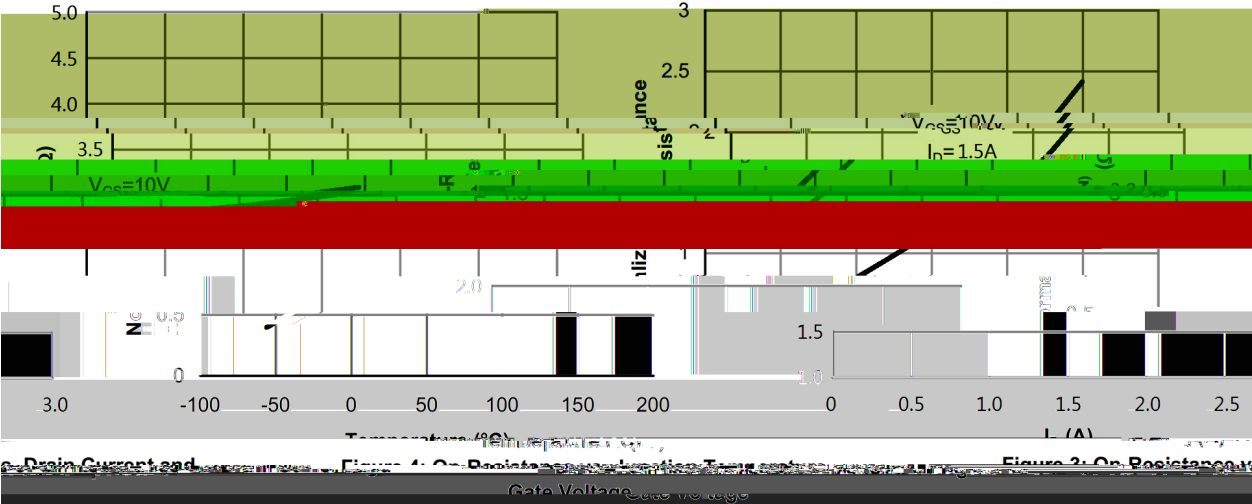
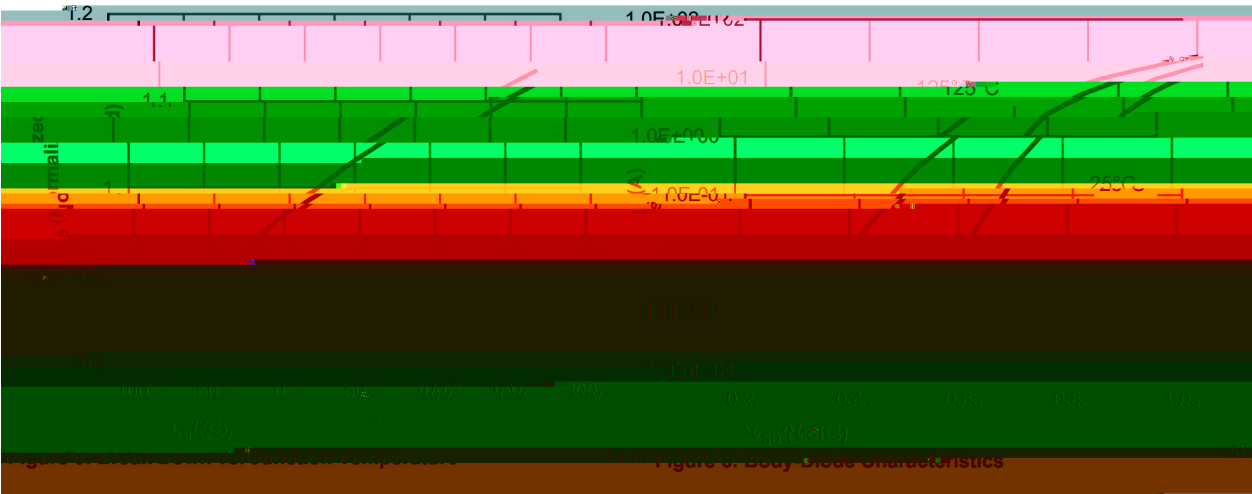
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	500	V
Drain Current	$I_D(T_c=25^\circ\text{C})$	1.4	A
Drain Current - Pulsed	I_{DM}	4.3	A
Gate-Source Voltage	V_{GS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	112.5	mJ
Avalanche Current	I_{AS}	4.5	A
Power Dissipation	$P_D(T_c=25^\circ\text{C})$	25	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	
Junction to Case	$R_{\theta JC}$	8.3	/W

/ Electrical Characteristics($T_a=25^\circ\text{C}$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS}=0V$ $I_D=250\mu A$	500			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=500V$ $V_{GS}=0V$			1	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 30V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2.0	3.0	4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=1.5A$		2.8	3.5	Ω
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=3.0A$			1.4	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		220		pF
Output Capacitance	C_{oss}			130		
Reverse Transfer Capacitance	C_{rss}			5		
Total Gate Charge	Q_G	$V_{DS}=400V$ $I_D=3.0A$ $V_{GS}=10V$		12.5		nC
Gate-Source Charge	Q_{GS}			3.2		
Gate-Drain Charge	Q_{GD}			4.2		

Parameter

/ Electrical Characteristic Curve



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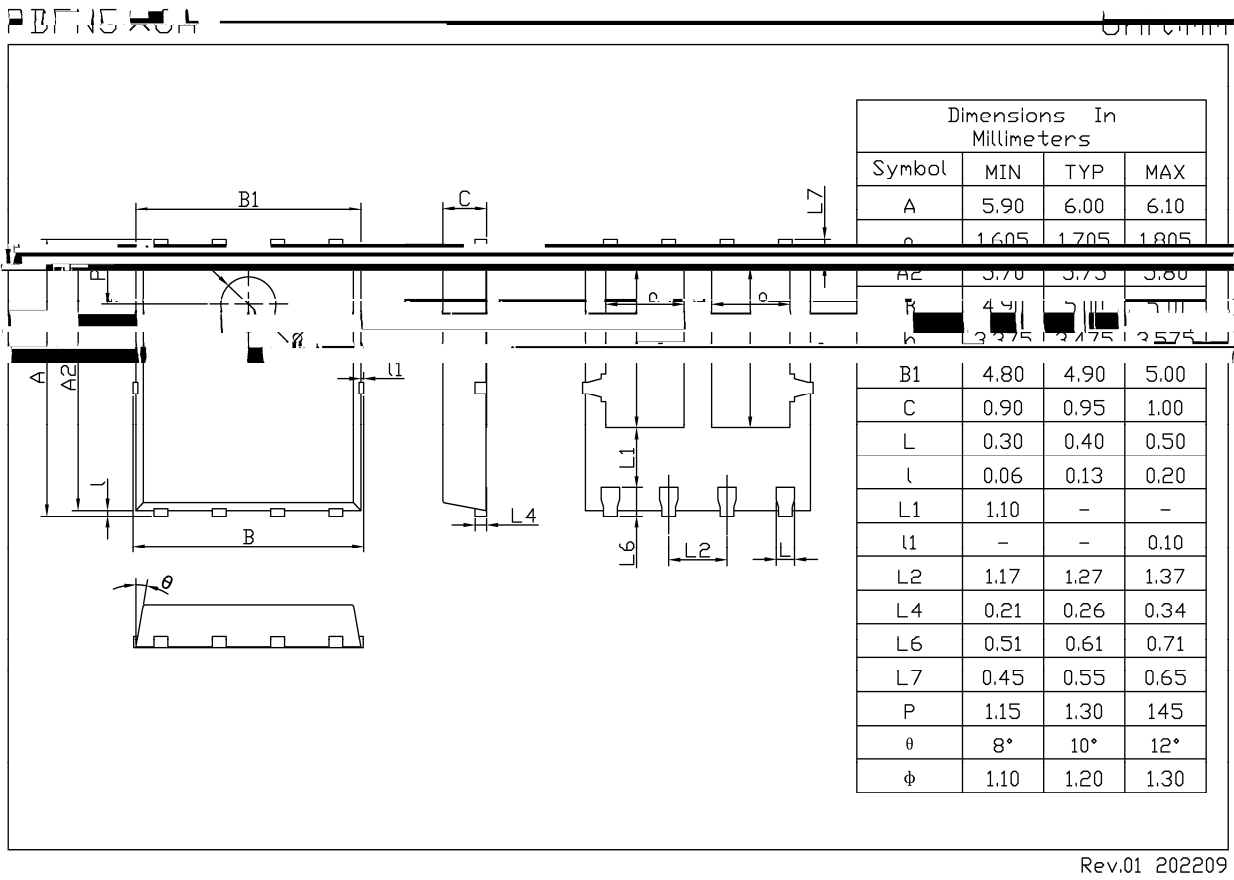
Rev.A Jul.-2024



蓝箭电子
BLUE ROCKET ELECTRONICS

DATA SHEET

I Package Dimensions



/ Marking Instructions



BR

3N50AF

Note

BR

Company Code

3N50AF

Product Type Code

****:

Lot No. Code, code change with Lot No

() / Temperature Profile for IR Reflow Soldering(Pb-Free)

- Note:

1

150 180

60 90sec;

2

245±5

5±0.5sec;

3

2 10 /sec.

1.Preheating:150~180 , Time:60~90sec.

2.Peak Temp.:245±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ Packaging SPEC.

/ REEL